

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
07 October 2021 (07.10.2021)



(10) International Publication Number
WO 2021/202335 A1

(51) International Patent Classification:

C23C 16/40 (2006.01) H01L 21/02 (2006.01)
C23C 16/50 (2006.01) C07F 7/18 (2006.01)

(21) International Application Number:

PCT/US2021/024581

(22) International Filing Date:

29 March 2021 (29.03.2021)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

63/003,068 31 March 2020 (31.03.2020) US
63/104,440 22 October 2020 (22.10.2020) US

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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ,
CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO,

(54) Title: NEW PRECURSORS FOR DEPOSITING FILMS WITH HIGH ELASTIC MODULUS

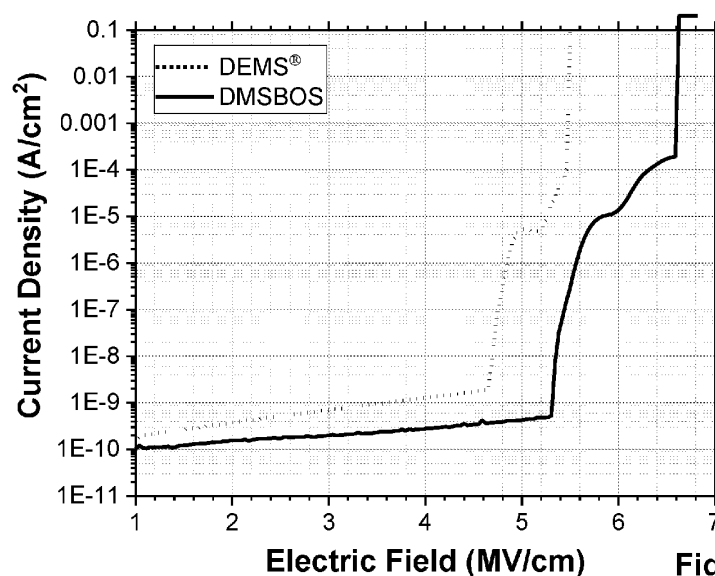


Figure 8

(57) Abstract: A method for making a dense organosilicon film with improved mechanical properties, the method comprising the steps of: providing a substrate within a reaction chamber; introducing into the reaction chamber a gaseous composition comprising hydri-
dodimethyl-alkoxysilane; and applying energy to the gaseous composition comprising hydridodimethyl-alkoxysilane in the reaction
chamber to induce reaction of the gaseous composition comprising hydrido-dimethyl-alkoxysilane to deposit an organosilicon film on
the substrate, wherein the organosilicon film has a dielectric constant from ~ 2.70 to ~ 3.50, an elastic 10 modulus of from ~ 6 to ~ 36
GPa, and an at. % carbon from ~ 10 to ~ 36 as measured by XPS.

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DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, IT, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

— with international search report (Art. 21(3))